

<b>V<sub>DSS</sub></b> , -30V <b>R<sub>DS(ON)</sub></b> , 9.5mΩ (max.) @ V <sub>GS</sub> =-10V <b>R<sub>DS(ON)</sub></b> , 15mΩ (max.) @ V <sub>GS</sub> =-4.5V <b>I<sub>D</sub></b> , -61A	<b>TO-252</b>	

Description	Features
The SG30P05D uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul style="list-style-type: none"> <li>• Low On-Resistance</li> <li>• Low Input Capacitance</li> <li>• Low Miller Charge</li> <li>• Low Input / Output Leakage</li> <li>• Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul style="list-style-type: none"> <li>• Lithium-Ion Secondary Batteries</li> <li>• Load Switch</li> <li>• DC-DC converters and Off-line UPS</li> </ul>

### Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG30P05D	Halogen-Free	TO-252	D	Tape & Reel	2,500

### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	T <sub>C</sub> =25°C	-61
		T <sub>C</sub> =100°C	-38
Drain Current-Pulsed <small>Note 1</small>	I <sub>DM</sub>	-67	A
Avalanche Current, L=0.1mH	I <sub>AS</sub>	-33	A
Avalanche Energy, L=0.1mH	E <sub>AS</sub>	54.5	mJ
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> =25°C	52.3
		T <sub>C</sub> =100°C	20.9
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range	T <sub>J</sub>	-55 to +150	°C

### Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Thermal resistance, Junction-to-Ambient <small>Note 2</small>	R <sub>θJA</sub>	Steady State	-	52.9	-	°C/W
Thermal resistance, Junction-to-Case	R <sub>θJC</sub>	Steady State	-	2.39	-	°C/W

## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250μA	-1.0	-	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-15A	-	-	9.5	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>DS</sub> =-7A	-	-	15	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	-	3875	-	pF
Output Capacitance	C <sub>oss</sub>		-	398	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	278	-	
Gate Resistance	R <sub>g</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	2.89	-	Ω

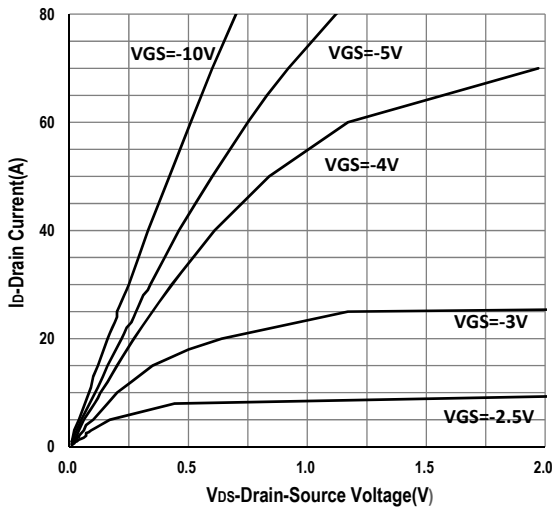
SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-20A	-	15.9	-	ns
Rise Time	t <sub>r</sub>		-	80.5	-	
Turn-Off Delay Time	T <sub>d(off)</sub>		-	96.2	-	
Fall Time	t <sub>f</sub>		-	81.3	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	63.5	-	nC
Gate to Source Gate Charge	Q <sub>gs</sub>		-	14.7	-	
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	8.83	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A	-	-	-1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	V <sub>DD</sub> =-15V, I <sub>F</sub> =-20A, di/dt=100A/μs	-	23.0	-	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	V <sub>DD</sub> =-15V, I <sub>F</sub> =-20A, di/dt=100A/μs	-	16.0	-	nC
Reverse Recovery Current	I <sub>RRM</sub>	V <sub>DD</sub> =-15V, I <sub>F</sub> =-20A, di/dt=100A/μs	-	1.27	-	A

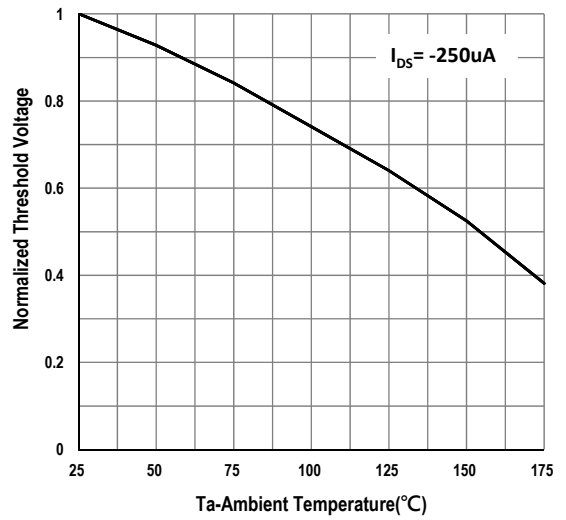
- Notes:**
- Pulse Test: Pulse Width ≤ 10ms, Duty Cycle ≤ 1%.
  - R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design. R<sub>θJA</sub> shown below for single device operation on FR-4 in still air.

## Typical Operating Characteristics

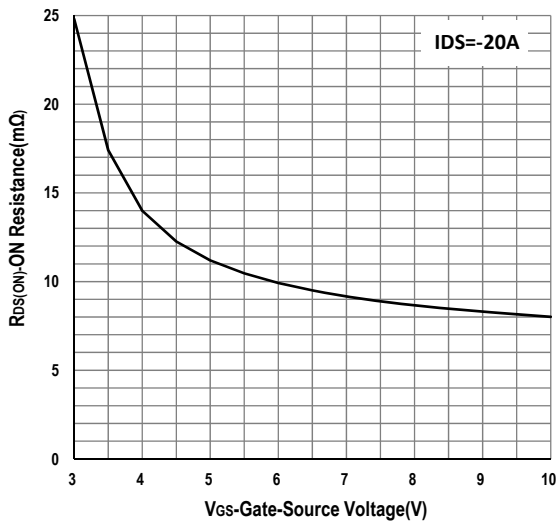
### Output Characteristics



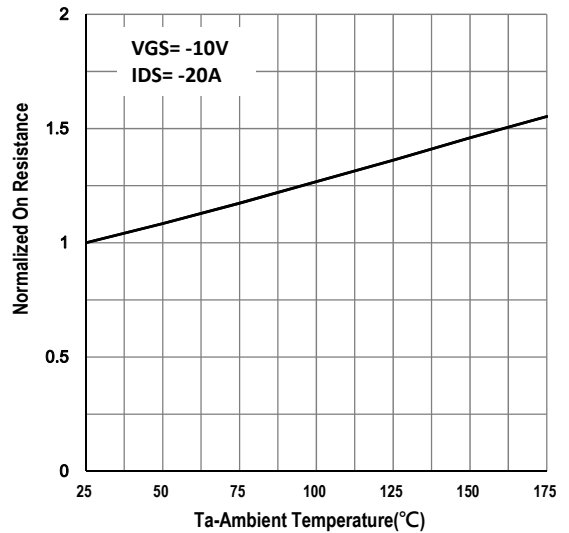
### Gate Threshold Voltage



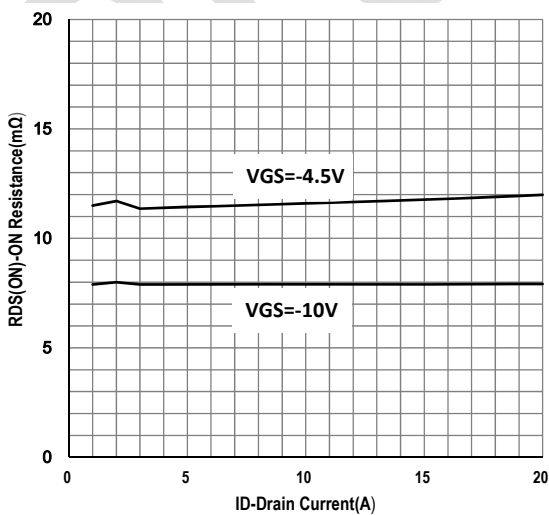
### Gate-Source On Resistance



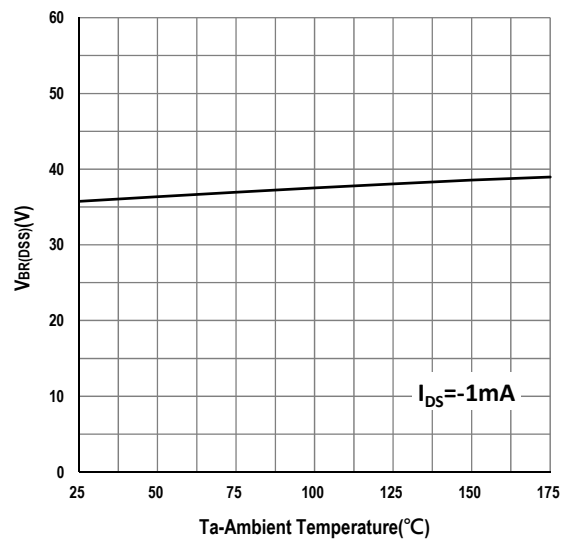
### Drain-Source On Resistance



### Drain-Source On Resistance

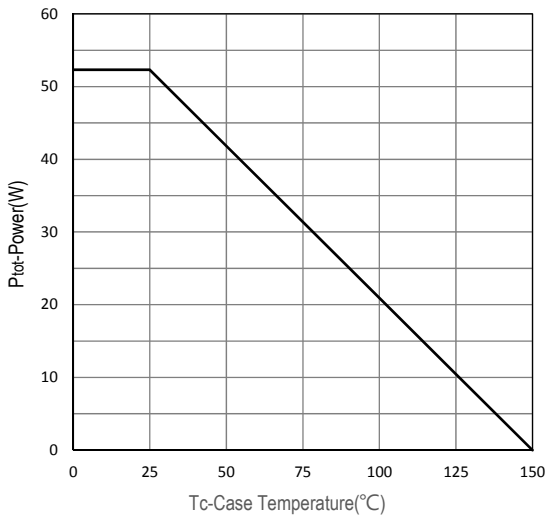


### Source-Drain Diode Forward

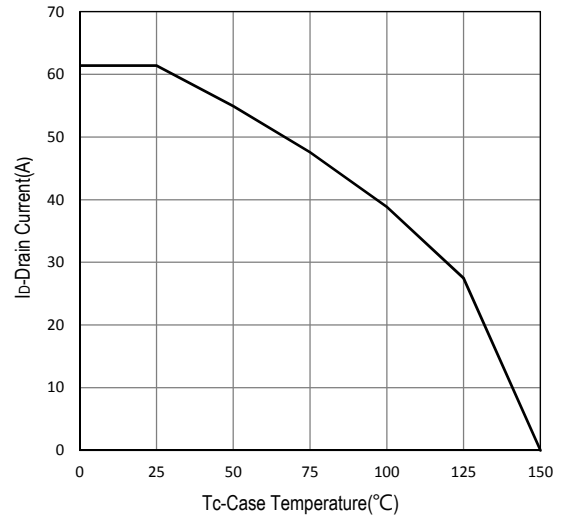


## Typical Operating Characteristics (Cont.)

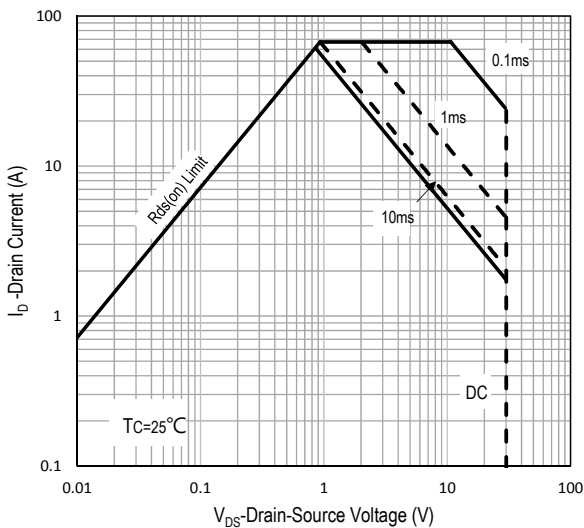
**Power Dissipation**



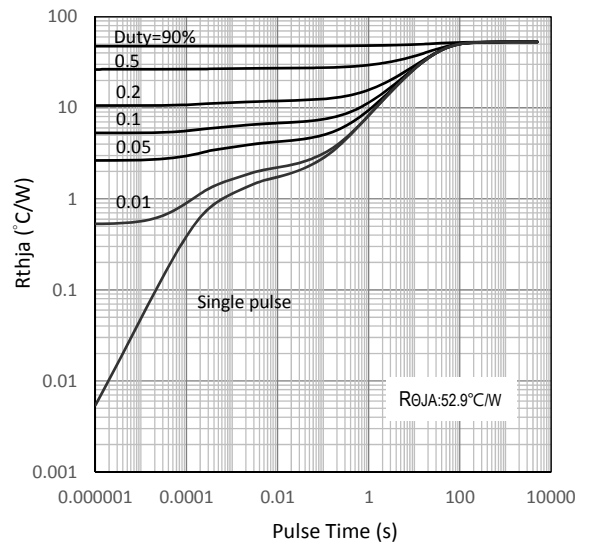
**Drain Current**



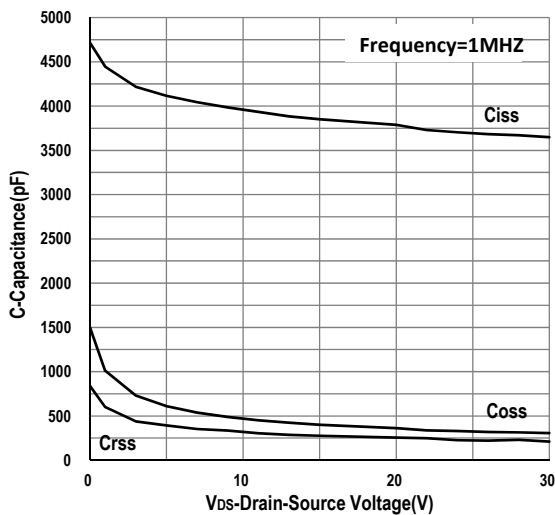
**Safe Operation Area**



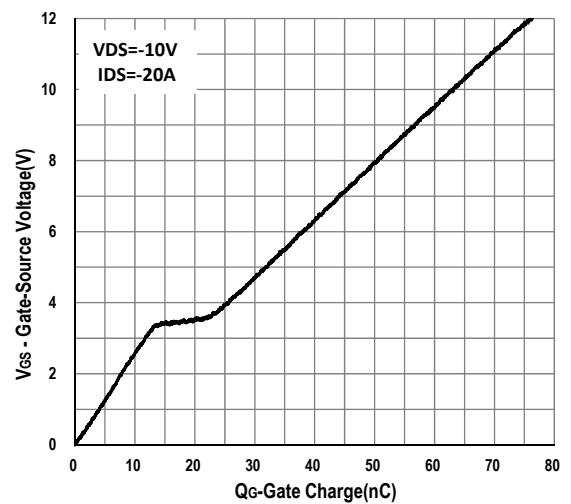
**Transient Thermal Impedance**



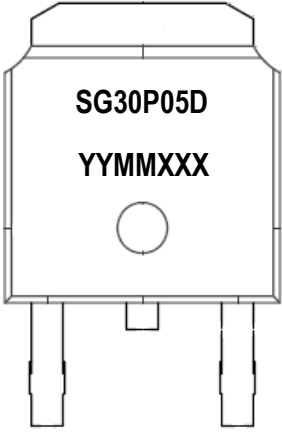
**Capacitance**



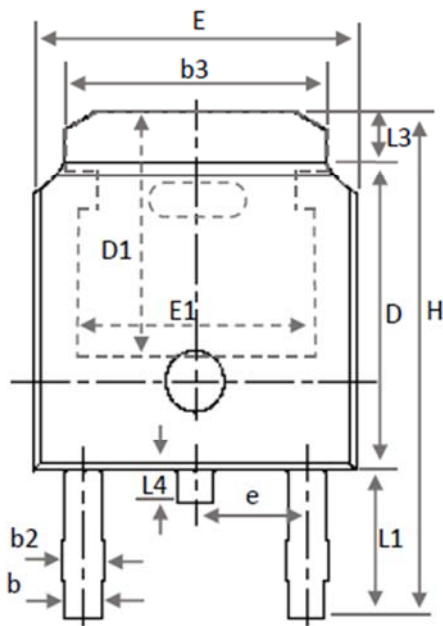
**Gate Charge**



**Marking Information**

TO-252 (D)	Marking Rule
<p>Laser Marking</p>  <p>The diagram shows a TO-252 (D) MOSFET package. On the top surface, there are two lines of laser marking: 'SG30P05D' and 'YYMMXXX'. The package has three leads extending from the bottom.</p>	<p><u>Line 1</u> : Device SG30P05D</p> <p><u>Line 2</u> : Date Code YYMMXXX</p> <p>YY : Year Code MM : Month Code XXX : Serial Number</p>

## Package of Dimension



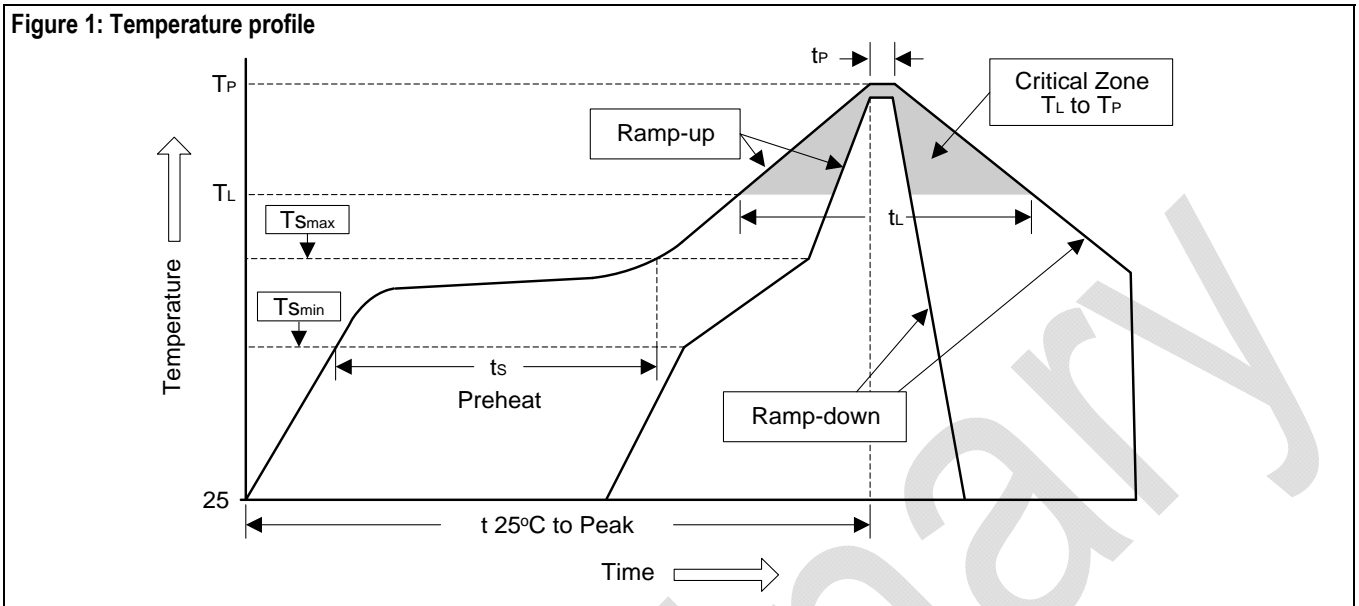
Symbol	Min	Nor	Max
E	6.35	6.54	6.731
L	1.40	1.59	1.78
L1	2.743 Ref.		
L2	0.508 BSC		
L3	0.89	1.08	1.27
L4	0.60	0.81	1.01
D	5.97	6.10	6.223
H	9.40	9.91	10.41
b	0.64	0.77	0.89
b2	0.76	0.95	1.14
b3	4.95	5.21	5.46
e	2.286 BSC		
A	2.18	2.29	2.39
A1	0.00	0.07	0.13
c2	0.46	0.68	0.89
D1	5.21	-	-
E1	4.32	-	-

1. All dimension are in millimeters.
2. Dimension does not include burrs and mold flash/protrusions.

## Soldering Methods for Silicongear's Products

1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T <sub>smin</sub> )	100°C	150°C
- Temperature Max (T <sub>smax</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
T <sub>smax</sub> to T <sub>L</sub>		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t <sub>P</sub> )	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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